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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

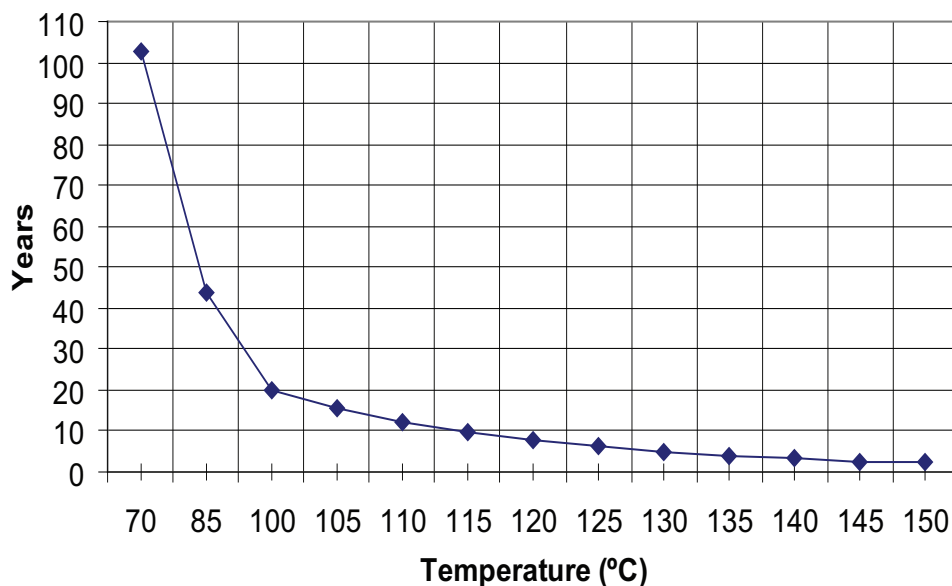
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	97
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p125-fg144

T _J (°C)	HTR Lifetime (yrs)
70	102.7
85	43.8
100	20.0
105	15.6
110	12.3
115	9.7
120	7.7
125	6.2
130	5.0
135	4.0
140	3.3
145	2.7
150	2.2



Note: HTR time is the period during which you would not expect a verify failure due to flash cell leakage.

Figure 2-1 • High-Temperature Data Retention (HTR)

Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature¹

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T _{STG} (°C)	Maximum Operating Junction Temperature T _J (°C) ²
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

1. This is a stress rating only; functional operation at any condition other than those indicated is not implied.

2. These limits apply for program/data retention only. Refer to [Table 2-1 on page 2-1](#) and [Table 2-2](#) for device operating conditions and absolute limits.

Table 2-4 • Overshoot and Undershoot Limits¹

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle ²	Maximum Overshoot/Undershoot ²
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. Based on reliability requirements at 85°C.

2. The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.

3. This table does not provide PCI overshoot/undershoot limits.

The absolute maximum junction temperature is 100°C. EQ 1 shows a sample calculation of the absolute maximum power dissipation allowed for a 484-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja} (\text{°C/W})} = \frac{100^{\circ}\text{C} - 70^{\circ}\text{C}}{20.5^{\circ}\text{C/W}} = 1.463 \text{ W}$$

EQ 1

Table 2-5 • Package Thermal Resistivities

Package Type	Device	Pin Count	θ_{jc}	θ_{ja}			Units
				Still Air	200 ft/min	500 ft/min	
Quad Flat No Lead	A3P030	132	0.4	21.4	16.8	15.3	°C/W
	A3P060	132	0.3	21.2	16.6	15.0	°C/W
	A3P125	132	0.2	21.1	16.5	14.9	°C/W
	A3P250	132	0.1	21.0	16.4	14.8	°C/W
Very Thin Quad Flat Pack (VQFP)	All devices	100	10.0	35.3	29.4	27.1	°C/W
Thin Quad Flat Pack (TQFP)	All devices	144	11.0	33.5	28.0	25.7	°C/W
Plastic Quad Flat Pack (PQFP)	All devices	208	8.0	26.1	22.5	20.8	°C/W
Fine Pitch Ball Grid Array (FBGA)	See note*	144	3.8	26.9	22.9	21.5	°C/W
	See note*	256	3.8	26.6	22.8	21.5	°C/W
	See note*	484	3.2	20.5	17.0	15.9	°C/W
	A3P1000	144	6.3	31.6	26.2	24.2	°C/W
	A3P1000	256	6.6	28.1	24.4	22.7	°C/W
	A3P1000	484	8.0	23.3	19.0	16.7	°C/W

Note: *This information applies to all ProASIC3 devices except the A3P1000. Detailed device/package thermal information will be available in future revisions of the datasheet.

Temperature and Voltage Derating Factors

Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays
 (normalized to $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.425 \text{ V}$)

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.88	0.93	0.95	1.00	1.02	1.04
1.500	0.83	0.88	0.90	0.95	0.96	0.98
1.575	0.80	0.84	0.87	0.91	0.93	0.94

Calculating Power Dissipation

Quiescent Supply Current

Table 2-7 • Quiescent Supply Current Characteristics

	A3P015	A3P030	A3P060	A3P125	A3P250	A3P400	A3P600	A3P1000
Typical (25°C)	2 mA	2 mA	2 mA	2 mA	3 mA	3 mA	5 mA	8 mA
Max. (Commercial)	10 mA	10 mA	10 mA	10 mA	20 mA	20 mA	30 mA	50 mA
Max. (Industrial)	15 mA	15 mA	15 mA	15 mA	30 mA	30 mA	45 mA	75 mA

Note: I_{DD} Includes V_{CC} , V_{PUMP} , V_{CCI} , and V_{MV} currents. Values do not include I/O static contribution, which is shown in [Table 2-11](#) and [Table 2-12](#) on page 2-9.

Power per I/O Pin

**Table 2-8 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings
Applicable to Advanced I/O Banks**

	VMV (V)	Static Power P_{DC2} (mW) ¹	Dynamic Power $PAC9$ (μW/MHz) ²
Single-Ended			
3.3 V LVTTTL / 3.3 V LVCMOS	3.3	–	16.22
3.3 V LVCMOS Wide Range ³	3.3	–	16.22
2.5 V LVCMOS	2.5	–	5.12
1.8 V LVCMOS	1.8	–	2.13
1.5 V LVCMOS (JESD8-11)	1.5	–	1.45
3.3 V PCI	3.3	–	18.11
3.3 V PCI-X	3.3	–	18.11
Differential			
LVDS	2.5	2.26	1.20
LVPECL	3.3	5.72	1.87

Notes:

1. P_{DC2} is the static power (where applicable) measured on VMV.
2. $PAC9$ is the total dynamic power measured on V_{CC} and VMV.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

**Table 2-9 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings
Applicable to Standard Plus I/O Banks**

	VMV (V)	Static Power P_{DC2} (mW) ¹	Dynamic Power $PAC9$ (μW/MHz) ²
Single-Ended			
3.3 V LVTTTL / 3.3 V LVCMOS	3.3	–	16.23
3.3 V LVCMOS Wide Range ³	3.3	–	16.23

Notes:

1. P_{DC2} is the static power (where applicable) measured on VMV.
2. $PAC9$ is the total dynamic power measured on V_{CC} and VMV.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

RAM Contribution— P_{MEMORY}

$$P_{\text{MEMORY}} = P_{\text{AC11}} * N_{\text{BLOCKS}} * F_{\text{READ-CLOCK}} * \beta_2 + P_{\text{AC12}} * N_{\text{BLOCK}} * F_{\text{WRITE-CLOCK}} * \beta_3$$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{\text{READ-CLOCK}}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations.

$F_{\text{WRITE-CLOCK}}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in [Table 2-17 on page 2-14](#).

PLL Contribution— P_{PLL}

$$P_{\text{PLL}} = P_{\text{DC4}} + P_{\text{AC13}} * F_{\text{CLKOUT}}$$

F_{CLKOUT} is the output clock frequency.¹

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
 - Bit 0 (LSB) = 100%
 - Bit 1 = 50%
 - Bit 2 = 25%
 - ...
 - Bit 7 (MSB) = 0.78125%
 - Average toggle rate = (100% + 50% + 25% + 12.5% + ... + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-16 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 2-17 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

1. The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($P_{\text{AC14}} * F_{\text{CLKOUT}}$ product) to the total PLL contribution.

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-22 • Summary of AC Measuring Points

Standard	Measuring Trip Point (V_{trip})
3.3 V LVTTTL / 3.3 V LVCMOS	1.4 V
3.3 V LVCMOS Wide Range	1.4 V
2.5 V LVCMOS	1.2 V
1.8 V LVCMOS	0.90 V
1.5 V LVCMOS	0.75 V
3.3 V PCI	0.285 * VCCI (RR)
	0.615 * VCCI (FF)
3.3 V PCI-X	0.285 * VCCI (RR)
	0.615 * VCCI (FF)

Table 2-23 • I/O AC Parameter Definitions

Parameter	Parameter Definition
t_{DP}	Data to Pad delay through the Output Buffer
t_{PY}	Pad to Data delay through the Input Buffer
t_{DOUT}	Data to Output Buffer delay through the I/O interface
t_{EOUT}	Enable to Output Buffer Tristate Control delay through the I/O interface
t_{DIN}	Input Buffer to Data delay through the I/O interface
t_{HZ}	Enable to Pad delay through the Output Buffer—High to Z
t_{ZH}	Enable to Pad delay through the Output Buffer—Z to High
t_{LZ}	Enable to Pad delay through the Output Buffer—Low to Z
t_{ZL}	Enable to Pad delay through the Output Buffer—Z to Low
t_{ZHS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to High
t_{ZLS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to Low

Table 2-24 • Summary of I/O Timing Characteristics—Software Default Settings
 –2 Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$,
 Worst-Case V_{CCI} (per standard)
 Advanced I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option ¹	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.64	0.03	0.76	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
3.3 V LVCMOS Wide Range ²	100 μA	12 mA	High	35	–	0.45	4.08	0.03	0.76	0.32	4.08	3.20	3.71	4.14	6.61	5.74	ns
2.5 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.66	0.03	0.98	0.32	2.71	2.56	2.47	2.57	4.38	4.23	ns
1.8 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.64	0.03	0.91	0.32	2.69	2.27	2.76	3.05	4.36	3.94	ns
1.5 V LVCMOS	12 mA	12 mA	High	35	–	0.45	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns
3.3 V PCI	Per PCI spec	–	High	10	25 ⁴	0.45	2.00	0.03	0.65	0.32	2.04	1.46	2.40	2.68	3.71	3.13	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 ⁴	0.45	2.00	0.03	0.62	0.32	2.04	1.46	2.40	2.68	3.71	3.13	ns
LVDS	24 mA	–	High	–	–	0.45	1.37	0.03	1.20	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	0.45	1.34	0.03	1.05	–	–	–	–	–	–	–	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
4. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-11 on page 2-64](#) for connectivity. This resistor is not required during normal operation.

Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings
 –2 Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$,
 Worst-Case V_{CCI} (per standard)
 Standard I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option ¹	Slew Rate	Capacitive Load (pF)	External Resistor	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8 mA	High	35	–	0.45	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns
3.3 V LVCMOS Wide Range ²	100 μA	8 mA	High	35	–	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns
2.5 V LVCMOS	8 mA	8 mA	High	35	–	0.45	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns
1.8 V LVCMOS	4 mA	4 mA	High	35	–	0.45	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns
1.5 V LVCMOS	2 mA	2 mA	High	35	–	0.45	5.71	0.03	1.06	0.32	4.71	5.71	1.83	1.83	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Timing Characteristics

Table 2-41 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
4 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
6 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
8 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
12 mA	Std.	0.66	3.53	0.04	1.02	0.43	3.60	2.82	3.21	3.58	5.83	5.06	ns
	–1	0.56	3.00	0.04	0.86	0.36	3.06	2.40	2.73	3.05	4.96	4.30	ns
	–2	0.49	2.64	0.03	0.76	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
16 mA	Std.	0.66	3.33	0.04	1.02	0.43	3.39	2.56	3.26	3.68	5.63	4.80	ns
	–1	0.56	2.83	0.04	0.86	0.36	2.89	2.18	2.77	3.13	4.79	4.08	ns
	–2	0.49	2.49	0.03	0.76	0.32	2.53	1.91	2.44	2.75	4.20	3.58	ns
24 mA	Std.	0.66	3.08	0.04	1.02	0.43	3.13	2.12	3.32	4.06	5.37	4.35	ns
	–1	0.56	2.62	0.04	0.86	0.36	2.66	1.80	2.83	3.45	4.57	3.70	ns
	–2	0.49	2.30	0.03	0.76	0.32	2.34	1.58	2.48	3.03	4.01	3.25	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-81 • 1.5 V LVC MOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.4\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	12.78	0.04	1.44	0.43	12.81	12.78	3.40	2.64	15.05	15.02	ns
	–1	0.56	10.87	0.04	1.22	0.36	10.90	10.87	2.89	2.25	12.80	12.78	ns
	–2	0.49	9.55	0.03	1.07	0.32	9.57	9.55	2.54	1.97	11.24	11.22	ns
4 mA	Std.	0.66	10.01	0.04	1.44	0.43	10.19	9.55	3.75	3.27	12.43	11.78	ns
	–1	0.56	8.51	0.04	1.22	0.36	8.67	8.12	3.19	2.78	10.57	10.02	ns
	–2	0.49	7.47	0.03	1.07	0.32	7.61	7.13	2.80	2.44	9.28	8.80	ns
6 mA	Std.	0.66	9.33	0.04	1.44	0.43	9.51	8.89	3.83	3.43	11.74	11.13	ns
	–1	0.56	7.94	0.04	1.22	0.36	8.09	7.56	3.26	2.92	9.99	9.47	ns
	–2	0.49	6.97	0.03	1.07	0.32	7.10	6.64	2.86	2.56	8.77	8.31	ns
8 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns
12 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-82 • 1.5 V LVC MOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.4\text{ V}$
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.83	0.04	1.42	0.43	6.42	7.83	2.71	2.55	8.65	10.07	ns
	–1	0.56	6.66	0.04	1.21	0.36	5.46	6.66	2.31	2.17	7.36	8.56	ns
	–2	0.49	5.85	0.03	1.06	0.32	4.79	5.85	2.02	1.90	6.46	7.52	ns
4 mA	Std.	0.66	4.84	0.04	1.42	0.43	4.49	4.84	3.03	3.13	6.72	7.08	ns
	–1	0.56	4.12	0.04	1.21	0.36	3.82	4.12	2.58	2.66	5.72	6.02	ns
	–2	0.49	3.61	0.03	1.06	0.32	3.35	3.61	2.26	2.34	5.02	5.28	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

Table 2-86 • Minimum and Maximum DC Input and Output Levels

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max., V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
Per PCI specification	Per PCI curves										10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in [Figure 2-11](#).

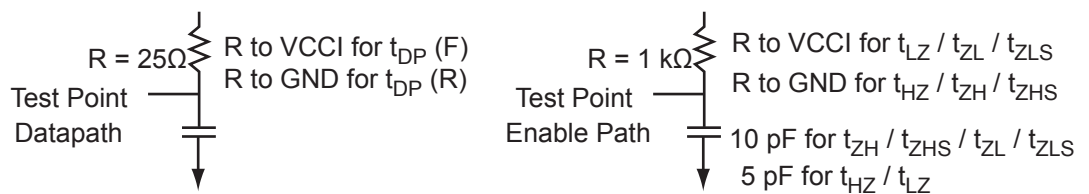


Figure 2-11 • AC Loading

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in [Table 2-87](#).

Table 2-87 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	3.3	0.285 * V _{CCI} for $t_{DP(R)}$ 0.615 * V _{CCI} for $t_{DP(F)}$	10

Note: *Measuring point = V_{trip} . See [Table 2-22 on page 2-22](#) for a complete table of trip points.

Table 2-96 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-15 on page 2-69 for more information.

Input Register

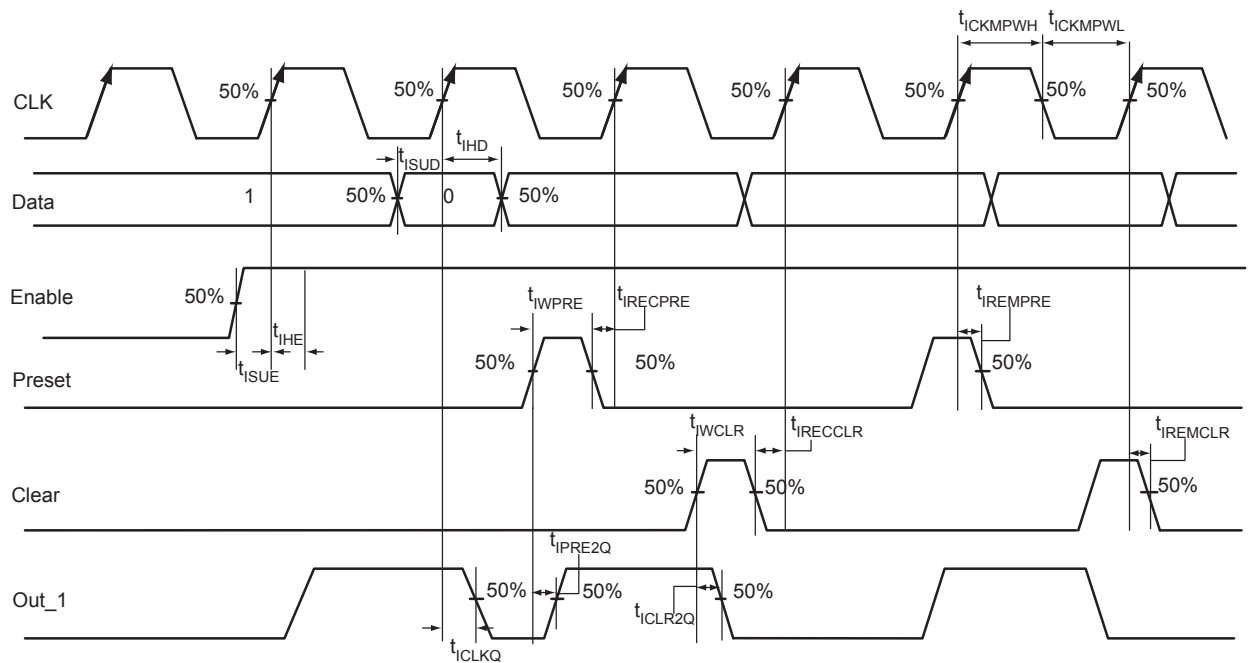


Figure 2-17 • Input Register Timing Diagram

Timing Characteristics

Table 2-98 • Input Data Register Propagation Delays
 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.24	0.27	0.32	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.26	0.30	0.35	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.37	0.42	0.50	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IEMCLR}	Asynchronous Clear Removal Time for the Input Data Register	0.00	0.00	0.00	ns
t_{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IEMPRE}	Asynchronous Preset Removal Time for the Input Data Register	0.00	0.00	0.00	ns
t_{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{ICKMPWH}	Clock Minimum Pulse Width High for the Input Data Register	0.36	0.41	0.48	ns
t_{ICKMPWL}	Clock Minimum Pulse Width Low for the Input Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

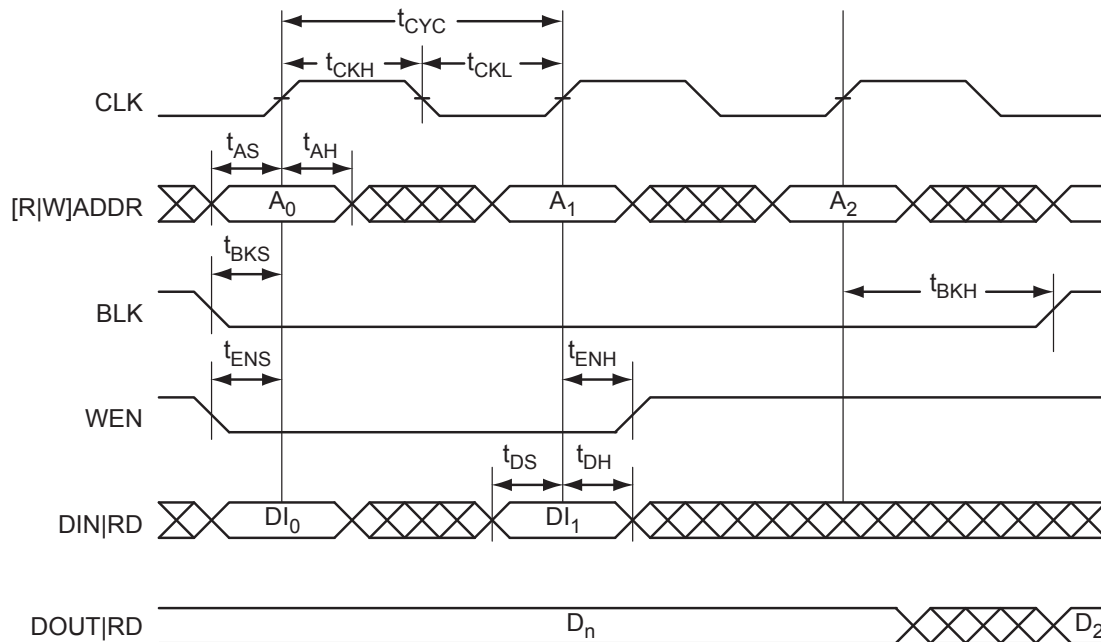


Figure 2-33 • RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.

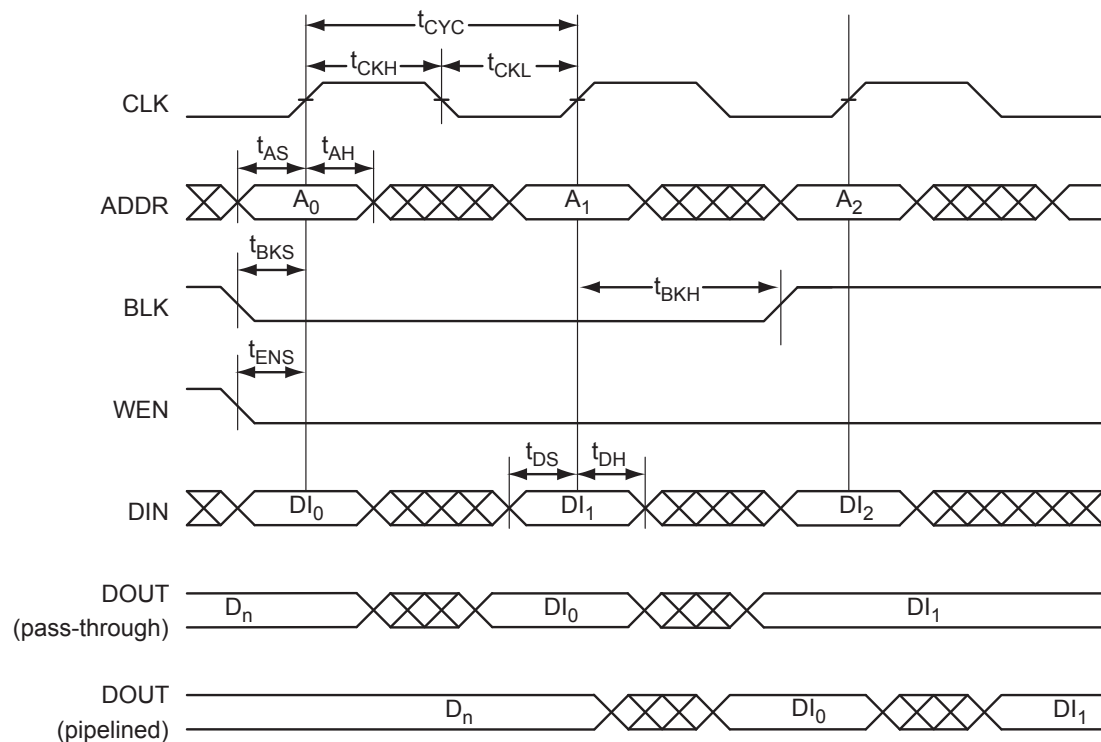


Figure 2-34 • RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 Only.

Table 2-119 • FIFO (for A3P250 only, aspect-ratio-dependent)
Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{ENS}	REN, WEN Setup Time	3.26	3.71	4.36	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	0.00	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.17	2.47	2.90	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.94	1.07	1.26	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
t_{REMRSTB}	RESET Removal	0.29	0.33	0.38	ns
t_{RECRSTB}	RESET Recovery	1.50	1.71	2.01	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency for FIFO	310	272	231	MHz

JTAG 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/O Characteristics" section on page 2-15 for more details.

Timing Characteristics

Table 2-125 • JTAG 1532

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{DISU}	Test Data Input Setup Time	0.50	0.57	0.67	ns
t_{DIHD}	Test Data Input Hold Time	1.00	1.13	1.33	ns
t_{TMSSU}	Test Mode Select Setup Time	0.50	0.57	0.67	ns
t_{TMDHD}	Test Mode Select Hold Time	1.00	1.13	1.33	ns
t_{TCK2Q}	Clock to Q (data out)	6.00	6.80	8.00	ns
t_{RSTB2Q}	Reset to Q (data out)	20.00	22.67	26.67	ns
F_{TCKMAX}	TCK Maximum Frequency	25.00	22.00	19.00	MHz
t_{TRSTREM}	ResetB Removal Time	0.00	0.00	0.00	ns
t_{TRSTREC}	ResetB Recovery Time	0.20	0.23	0.27	ns
t_{TRSTMPW}	ResetB Minimum Pulse	TBD	TBD	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

In critical applications, an upset in the JTAG circuit could allow entrance to an undesired JTAG state. In such cases, Microsemi recommends tying off TRST to GND through a resistor placed close to the FPGA pin.

Note that to operate at all VJTAG voltages, 500 Ω to 1 k Ω will satisfy the requirements.

Special Function Pins

NC **No Connect**

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

DC **Do Not Connect**

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

Related Documents

User's Guides

ProASIC FPGA Fabric User's Guide

http://www.microsemi.com/soc/documents/PA3_UG.pdf

Packaging

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

http://www.microsemi.com/soc/documents/ProdCat_PIB.pdf

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

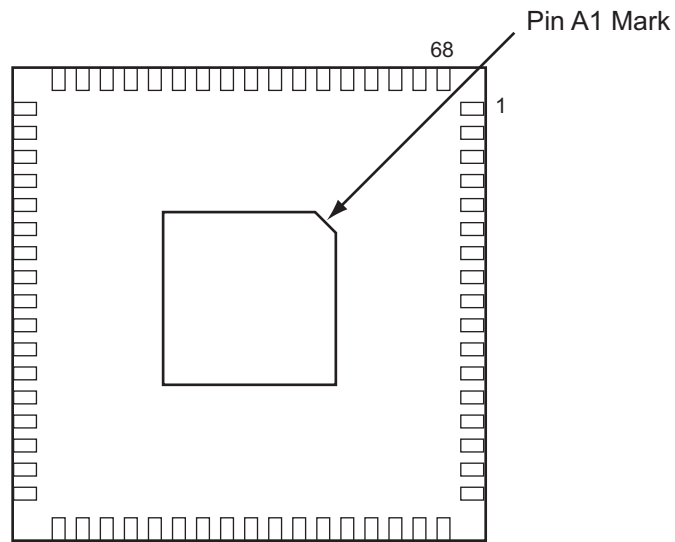
Package Mechanical Drawings

<http://www.microsemi.com/soc/documents/PckgMechDrwns.pdf>

This document contains the package mechanical drawings for all packages currently or previously supplied by Actel. Use the bookmarks to navigate to the package mechanical drawings.

Additional packaging materials are at <http://www.microsemi.com/products/solutions/package/docs.aspx>.

QN68 – Bottom View



Note: The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

QN132	
Pin Number	A3P125 Function
A1	GAB2/IO69RSB1
A2	IO130RSB1
A3	VCCIB1
A4	GFC1/IO126RSB1
A5	GFB0/IO123RSB1
A6	VCCPLF
A7	GFA1/IO121RSB1
A8	GFC2/IO118RSB1
A9	IO115RSB1
A10	VCC
A11	GEB1/IO110RSB1
A12	GEA0/IO107RSB1
A13	GEC2/IO104RSB1
A14	IO100RSB1
A15	VCC
A16	IO99RSB1
A17	IO96RSB1
A18	IO94RSB1
A19	IO91RSB1
A20	IO85RSB1
A21	IO79RSB1
A22	VCC
A23	GDB2/IO71RSB1
A24	TDI
A25	TRST
A26	GDC1/IO61RSB0
A27	VCC
A28	IO60RSB0
A29	GCC2/IO59RSB0
A30	GCA2/IO57RSB0
A31	GCA0/IO56RSB0
A32	GCB1/IO53RSB0
A33	IO49RSB0
A34	VCC
A35	IO44RSB0
A36	GBA2/IO41RSB0

QN132	
Pin Number	A3P125 Function
A37	GBB1/IO38RSB0
A38	GBC0/IO35RSB0
A39	VCCIB0
A40	IO28RSB0
A41	IO22RSB0
A42	IO18RSB0
A43	IO14RSB0
A44	IO11RSB0
A45	IO07RSB0
A46	VCC
A47	GAC1/IO05RSB0
A48	GAB0/IO02RSB0
B1	IO68RSB1
B2	GAC2/IO131RSB1
B3	GND
B4	GFC0/IO125RSB1
B5	VCOMPLF
B6	GND
B7	GFB2/IO119RSB1
B8	IO116RSB1
B9	GND
B10	GEB0/IO109RSB1
B11	VMV1
B12	GEB2/IO105RSB1
B13	IO101RSB1
B14	GND
B15	IO98RSB1
B16	IO95RSB1
B17	GND
B18	IO87RSB1
B19	IO81RSB1
B20	GND
B21	GNDQ
B22	TMS
B23	TDO
B24	GDC0/IO62RSB0

QN132	
Pin Number	A3P125 Function
B25	GND
B26	NC
B27	GCB2/IO58RSB0
B28	GND
B29	GCB0/IO54RSB0
B30	GCC1/IO51RSB0
B31	GND
B32	GBB2/IO43RSB0
B33	VMV0
B34	GBA0/IO39RSB0
B35	GBC1/IO36RSB0
B36	GND
B37	IO26RSB0
B38	IO21RSB0
B39	GND
B40	IO13RSB0
B41	IO08RSB0
B42	GND
B43	GAC0/IO04RSB0
B44	GNDQ
C1	GAA2/IO67RSB1
C2	IO132RSB1
C3	VCC
C4	GFB1/IO124RSB1
C5	GFA0/IO122RSB1
C6	GFA2/IO120RSB1
C7	IO117RSB1
C8	VCCIB1
C9	GEA1/IO108RSB1
C10	GNDQ
C11	GEA2/IO106RSB1
C12	IO103RSB1
C13	VCCIB1
C14	IO97RSB1
C15	IO93RSB1
C16	IO89RSB1

TQ144	
Pin Number	A3P060 Function
109	NC
110	NC
111	GBA1/IO24RSB0
112	GBA0/IO23RSB0
113	GBB1/IO22RSB0
114	GBB0/IO21RSB0
115	GBC1/IO20RSB0
116	GBC0/IO19RSB0
117	VCCIB0
118	GND
119	VCC
120	IO18RSB0
121	IO17RSB0
122	IO16RSB0
123	IO15RSB0
124	IO14RSB0
125	IO13RSB0
126	IO12RSB0
127	IO11RSB0
128	NC
129	IO10RSB0
130	IO09RSB0
131	IO08RSB0
132	GAC1/IO07RSB0
133	GAC0/IO06RSB0
134	NC
135	GND
136	NC
137	GAB1/IO05RSB0
138	GAB0/IO04RSB0
139	GAA1/IO03RSB0
140	GAA0/IO02RSB0
141	IO01RSB0
142	IO00RSB0
143	GNDQ
144	VMV0

Revision	Changes	Page
Revision 13 (January 2013)	The "ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43104).	1-IV
	Added a note to Table 2-2 • Recommended Operating Conditions 1 (SAR 43644): The programming temperature range supported is $T_{\text{ambient}} = 0^{\circ}\text{C}$ to 85°C .	2-2
	The note in Table 2-115 • ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42569).	2-90
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40284). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The Security section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1
	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information" to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions 1 (SAR 38321).	2-1 2-2
	Table 2-35 • Duration of Short Circuit Event Before Failure was revised to change the maximum temperature from 110°C to 100°C , with an example of six months instead of three months (SAR 37933).	2-31
	In Table 2-93 • Minimum and Maximum DC Input and Output Levels, VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 28549).	2-68
	Figure 2-37 • FIFO Read and Figure 2-38 • FIFO Write are new (SAR 28371).	2-99
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38321). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1